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60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ C$
60V	68mΩ @ $V_{GS} = 10V$	5.6A
	100mΩ @ $V_{GS} = 4.5V$	4.7A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

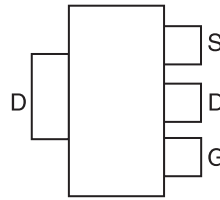
Applications

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

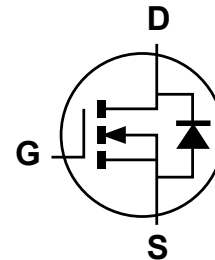
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

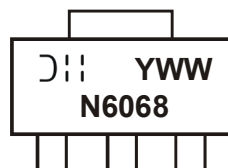
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame.
Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.112 grams (approximate)

Ordering Information (Note 4 & 5)

Part Number	Qualification	Case	Packaging
DMN6068SE-13	Standard	SOT223	4000 / Tape & Reel
DMN6068SEQ-13	Automotive	SOT223	4000 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.
 5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

Marking Information



⑆ = Manufacturer's Marking
 N6068 = Product Type Marking Code
 YWW = Date Code Marking
 Y = Year (ex: 9 = 2009)
 WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

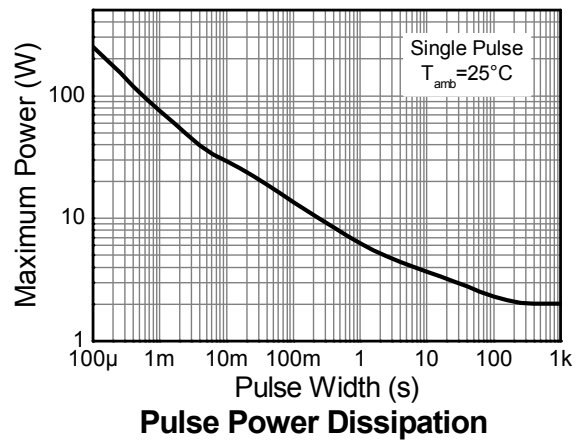
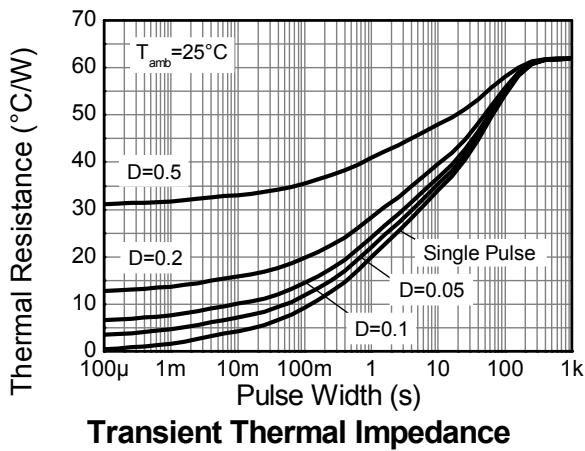
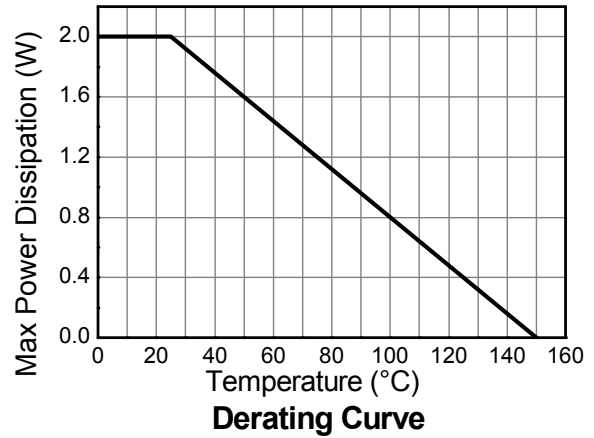
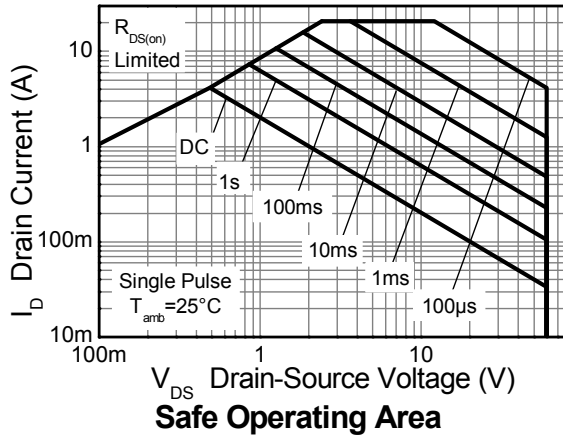
Characteristic		Symbol	Value	Unit	
Drain-Source voltage		V_{DSS}	60	V	
Gate-Source voltage	(Note 6)	V_{GS}	± 20	V	
Single Pulsed Avalanche Energy	(Note 11)	E_{AS}	37.5	mJ	
Single Pulsed Avalanche Current	(Note 11)	I_{AS}	5.0	A	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 8)	5.6	A	
		$T_A = +70^\circ\text{C}$ (Note 8)	4.5		
		(Note 7)	4.1		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 9)	I_{DM}	20.8	A
Continuous Source current (Body diode)		(Note 8)	I_S	4.9	A
Pulsed Source current (Body diode)		(Note 9)	I_{SM}	20.8	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 7)	P_D	2.0	W mW/ $^\circ\text{C}$
			16.0	
	(Note 8)		3.7 29.5	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
	(Note 8)		34	
Thermal Resistance, Junction to Lead	(Note 10)	$R_{\theta JL}$	11.5	
Operating and storage temperature range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
6. AEC-Q101 V_{GS} maximum is $\pm 16\text{V}$.
 7. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 8. Same as note (3), except the device is measured at $t \leq 10$ sec.
 9. Same as note (3), except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 10. Thermal resistance from junction to solder-point (at the end of the drain lead).
 11. UIS in production with $L = 3.0\text{mH}$, $I_{AS} = 5.0\text{A}$, $R_G = 25\Omega$, $V_{DD} = 50\text{V}$, starting $T_J = +25^\circ\text{C}$.

Thermal Characteristics

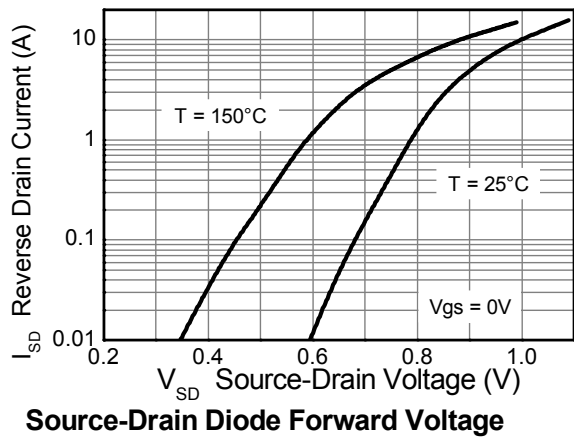
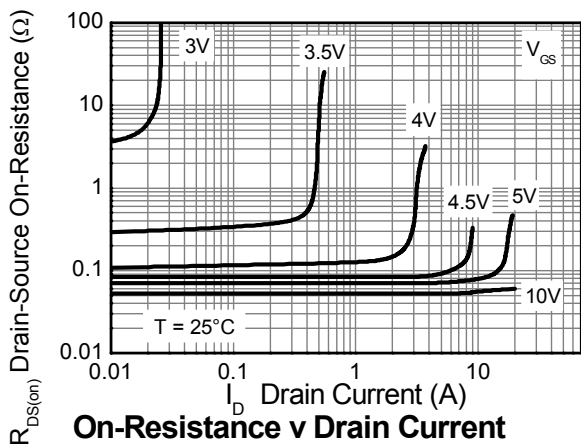
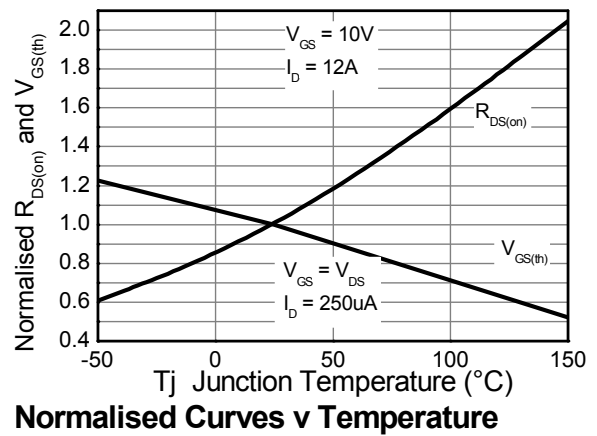
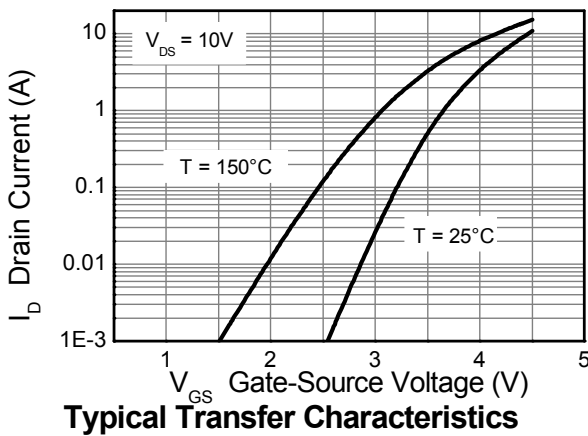
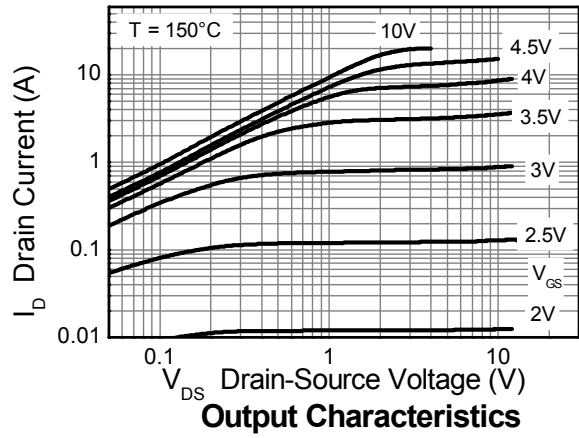
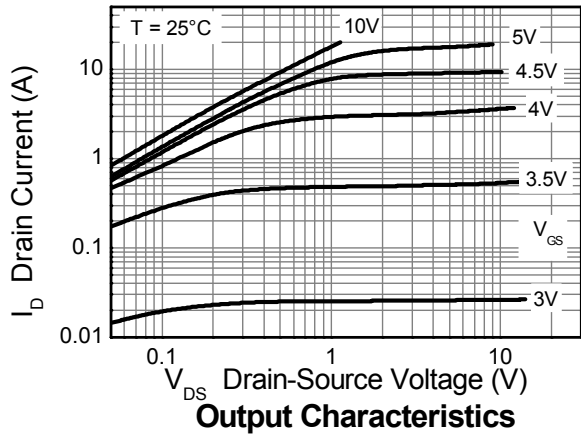


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

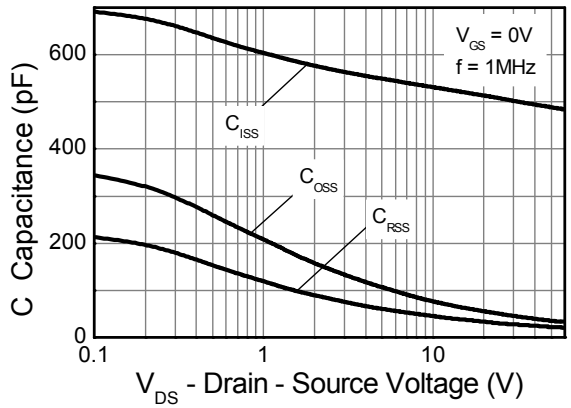
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 12)	R _{DS(on)}	—	—	0.068	Ω	V _{GS} = 10V, I _D = 12A
				0.100		V _{GS} = 4.5V, I _D = 6A
Forward Transconductance (Notes 12 & 13)	g _{fs}	—	19.7	—	S	V _{DS} = 15V, I _D = 12A
Diode Forward Voltage (Note 12)	V _{SD}	—	0.98	1.15	V	I _S = 12A, V _{GS} = 0V
Reverse recovery time (Note 13)	t _{rr}	—	145	—	ns	I _S = 12A, di/dt = 100A/μs
Reverse recovery charge (Note 13)	Q _{rr}	—	929	—	nC	
DYNAMIC CHARACTERISTICS (Note 13)						
Input Capacitance	C _{iSS}	—	502	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	45.7	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	27.1	—	pF	
Total Gate Charge (Note 14)	Q _g	—	5.55	—	nC	V _{GS} = 4.5V
Total Gate Charge (Note 14)	Q _g	—	10.3	—	nC	V _{GS} = 10V
Gate-Source Charge (Note 14)	Q _{gs}	—	1.6	—	nC	
Gate-Drain Charge (Note 14)	Q _{gd}	—	3.5	—	nC	
Turn-On Delay Time (Note 14)	t _{D(on)}	—	3.6	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 12A, R _G = 6.0Ω
Turn-On Rise Time (Note 14)	t _r	—	10.8	—	ns	
Turn-Off Delay Time (Note 14)	t _{D(off)}	—	11.9	—	ns	
Turn-Off Fall Time (Note 14)	t _f	—	8.7	—	ns	

Notes: 12. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.

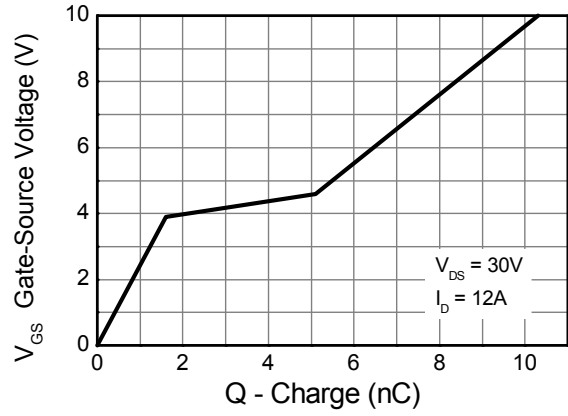
Typical Characteristics



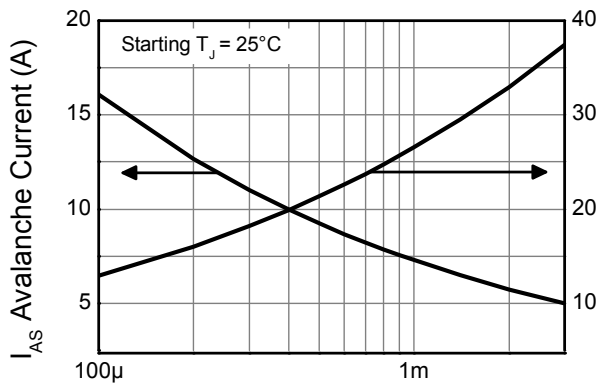
Typical Characteristics (cont.)



Capacitance v Drain-Source Voltage



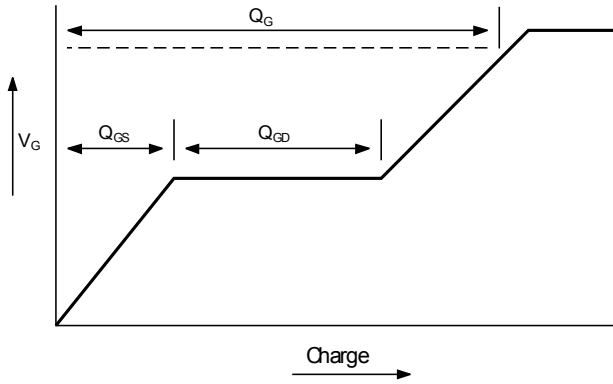
Gate-Source Voltage v Gate Charge



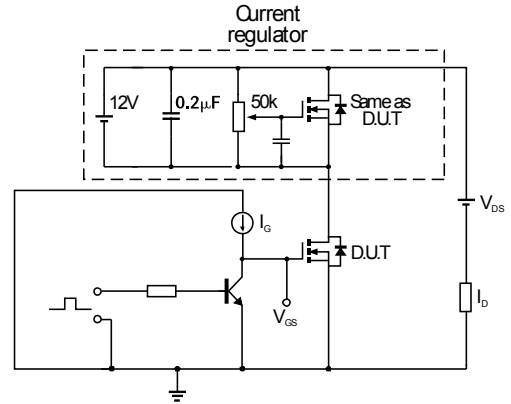
Single-Pulsed Avalanche Rating

E_{AS} Avalanche Energy (mJ)

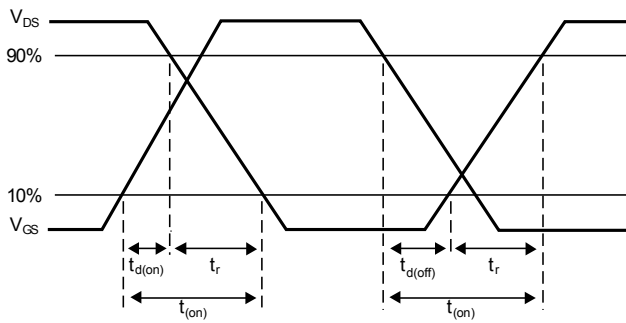
Test Circuits



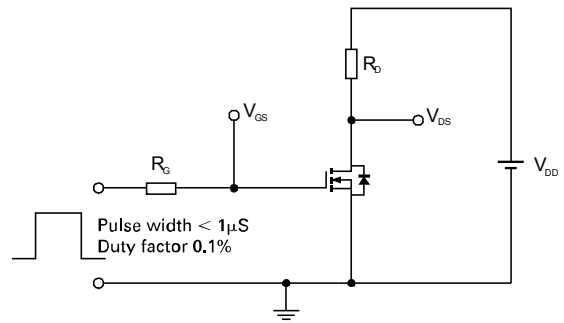
Basic gate charge waveform



Gate charge test circuit



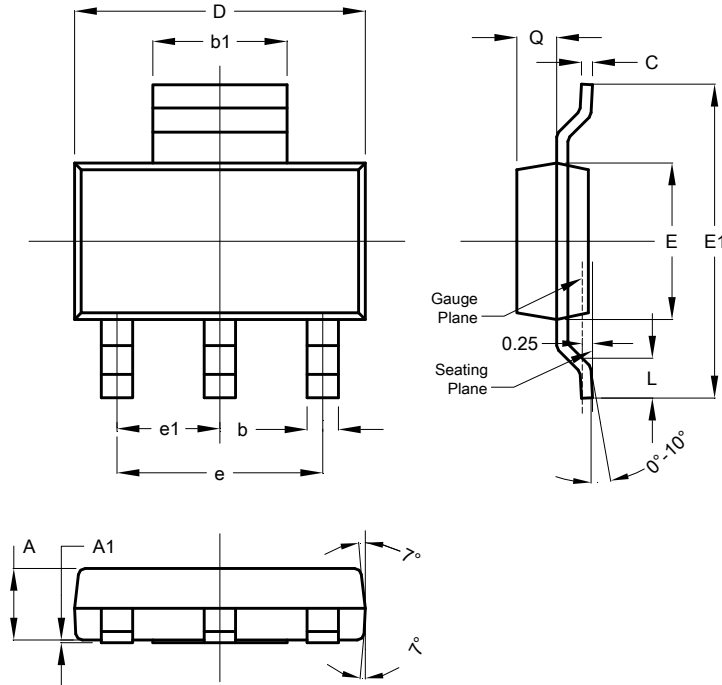
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

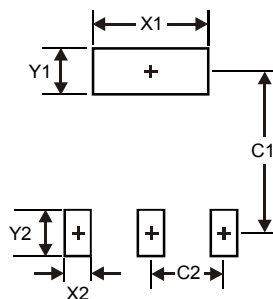
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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